



MPD07N65A

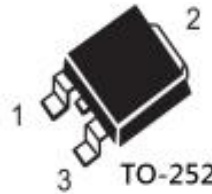
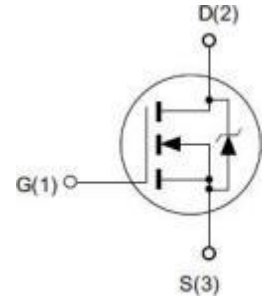
N-Channel Power MOSFET

Features

- ◆ 650V, 7A, $R_{DS(ON)}(Typ.) = 1.15\Omega @ V_{GS} = 10V$.
- ◆ Low C_{rss}
- ◆ Fast Switching
- ◆ 100% Avalanche Tested

Application

- ◆ Adapter
- ◆ LCD Panel Power
- ◆ E-Bike Charger
- ◆ Switching Mode Power Supply



Absolute Maximum Ratings $T_c = 25.0\text{C}$ unless otherwise noted

Symbol	Parameter	Limit	Unit
V_{DS}	Drain-Source Voltage ^a	650	V
V_{GS}	Gate-Source Voltage	± 30	V
I_D	Drain Current-Continuous, $T_c = 25^\circ\text{C}$	7	A
	Drain Current-Continuous, $T_c = 100^\circ\text{C}$	4	A
I_{DM}	Drain Current-Pulsed ^b	28	A
P_D	Maximum Power Dissipation @ $T_J = 25^\circ\text{C}$	69	W
EAS	Single Pulsed Avalanche Energy ^d	125	mJ
T_J, T_{STG}	Operating and Store Temperature Range	-55 to 150	$^\circ\text{C}$

Thermal Characteristics

Symbol	Parameter	Value	Unit
$R_{\theta JC}$	Thermal Resistance, Junction-Case Max.	1.8	$^\circ\text{C/W}$
$R_{\theta JA}$	Thermal Resistance Junction-Ambient Max.	60	$^\circ\text{C/W}$

Electrical Characteristics $T_J = 25.0\text{C}$ unless otherwise noted

■ Off Characteristics

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = 250\mu\text{A}$	650	-	-	V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 650V, V_{GS} = 0V$	-	-	1	μA
I_{GSS}	Forward Gate Body Leakage Current	$V_{DS} = 0V, V_{GS} = \pm 30V$	-	-	± 100	nA



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■ On Characteristics

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Unit
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_D=250\mu A$	2	-	4	V
$R_{DS(on)}$	Static Drain-Source On-Resistance ^c	$V_{GS}=10V, I_D=3.5A$	-	1.15	1.35	Ω

■ Dynamic Characteristics

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Unit
C_{iss}	Input Capacitance	$V_{DS}=25V, V_{GS}=0V, f=1.0MHz$	-	1089	-	pF
C_{oss}	Output Capacitance		-	100	-	pF
C_{rss}	Reverse Transfer Capacitance		-	14	-	pF

■ On Characteristics

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-On Delay Time	$V_{DD}=325V, I_D=7A, R_G=10\Omega, V_{GS}=10V$	-	19	-	ns
t_r	Turn-On Rise Time		-	29	-	ns
$t_{d(off)}$	Turn-Off Delay Time		-	78	-	ns
t_f	Turn-Off Fall Time		-	35	-	ns
Q_g	Total Gate Charge	$V_{DS}=520V, I_D=7A, V_{GS}=10V$	-	27	-	nC
Q_{gs}	Gate-Source Charge		-	6	-	nC
Q_{gd}	Gate-Drain Charge		-	11	-	nC

■ Drain-Source Diode Characteristics

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Unit
I_S	Drain-Source Diode Forward Continuous Current	$V_{GS}=0V$	-	-	7	A
I_{SM}	Maximum Pulsed Current	$V_{GS}=0V$	-	-	28	A
V_{SD}	Drain-Source Diode Forward Voltage	$V_{GS}=0V, I_S=7A$	-	-	1.4	V
T_{rr}	Body Diode Reverse Recovery Time	$di/dt=100A/us, I_S=7A, V_{GS}=0V$	-	340	-	ns
Q_{rr}	Reverse Recovery Charge		-	2900	-	nC

Notes:

- $T_J=-55\text{ }^\circ\text{C}$ to $+150\text{ }^\circ\text{C}$.
- Repetitive rating; pulse width limited by maximum junction temperature.
- Pulse width $\leq 300\mu s$; duty cycle $\leq 2\%$.
- $L=10mH, V_{DD}=50V, I_{as}=5A, R_G=25\Omega$ Starting $T_J=25\text{ }^\circ\text{C}$.



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Characteristic Curve

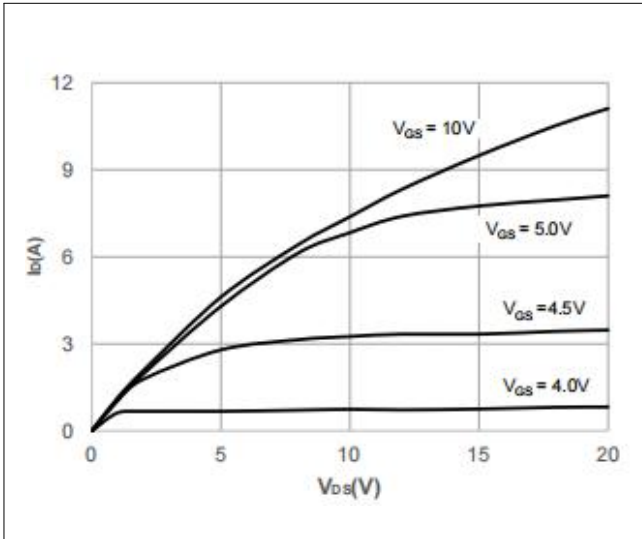


Figure 1. Typical Output Characteristics

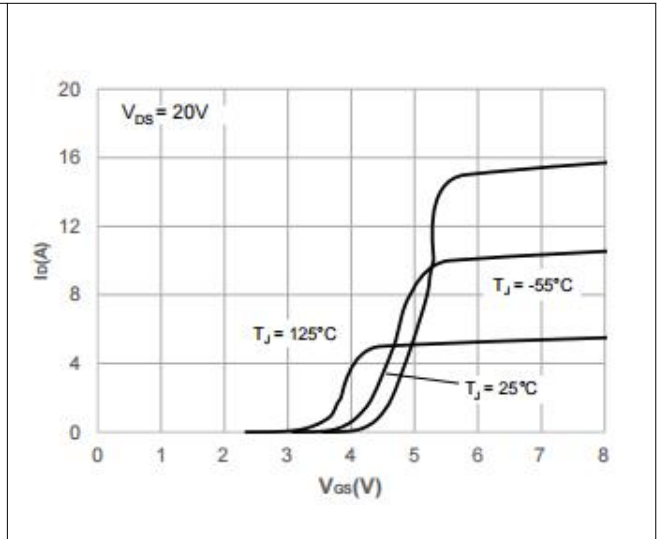


Figure 2. Typical Transfer Characteristics

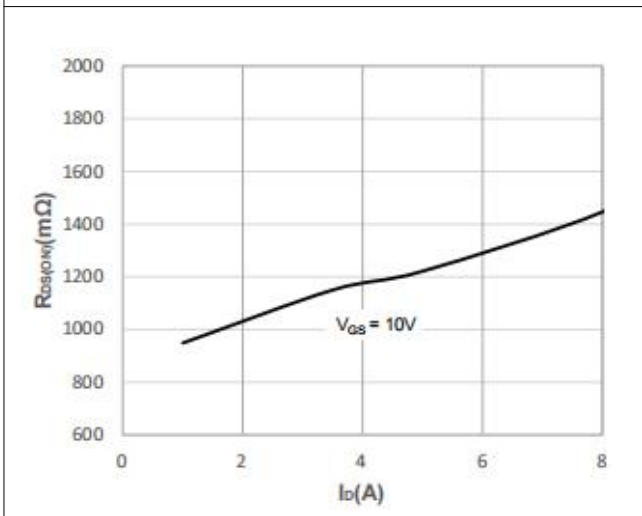


Figure 3. On-Resistance vs. Drain Current

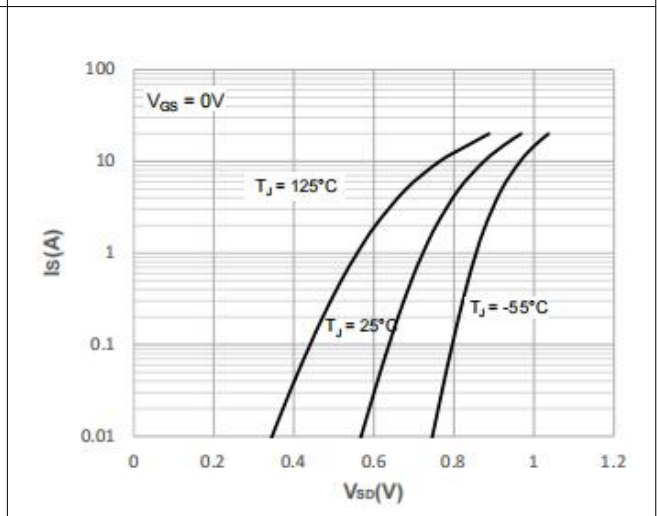


Figure 4. Body-Diode Characteristics

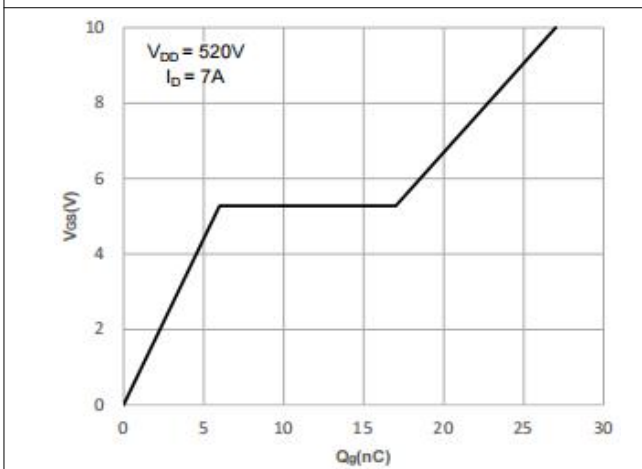


Figure 5. Gate-Charge Characteristics

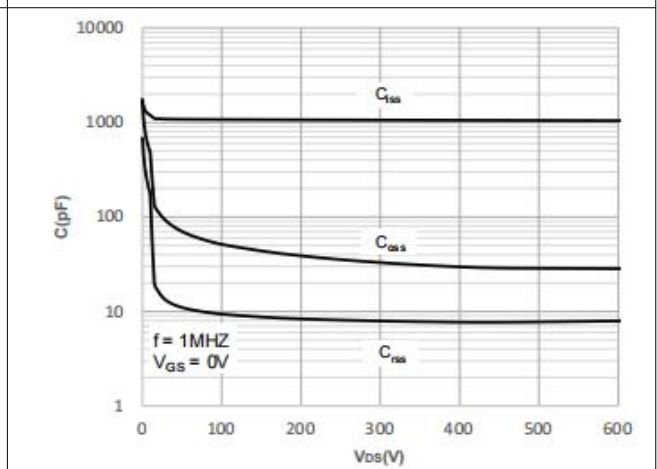


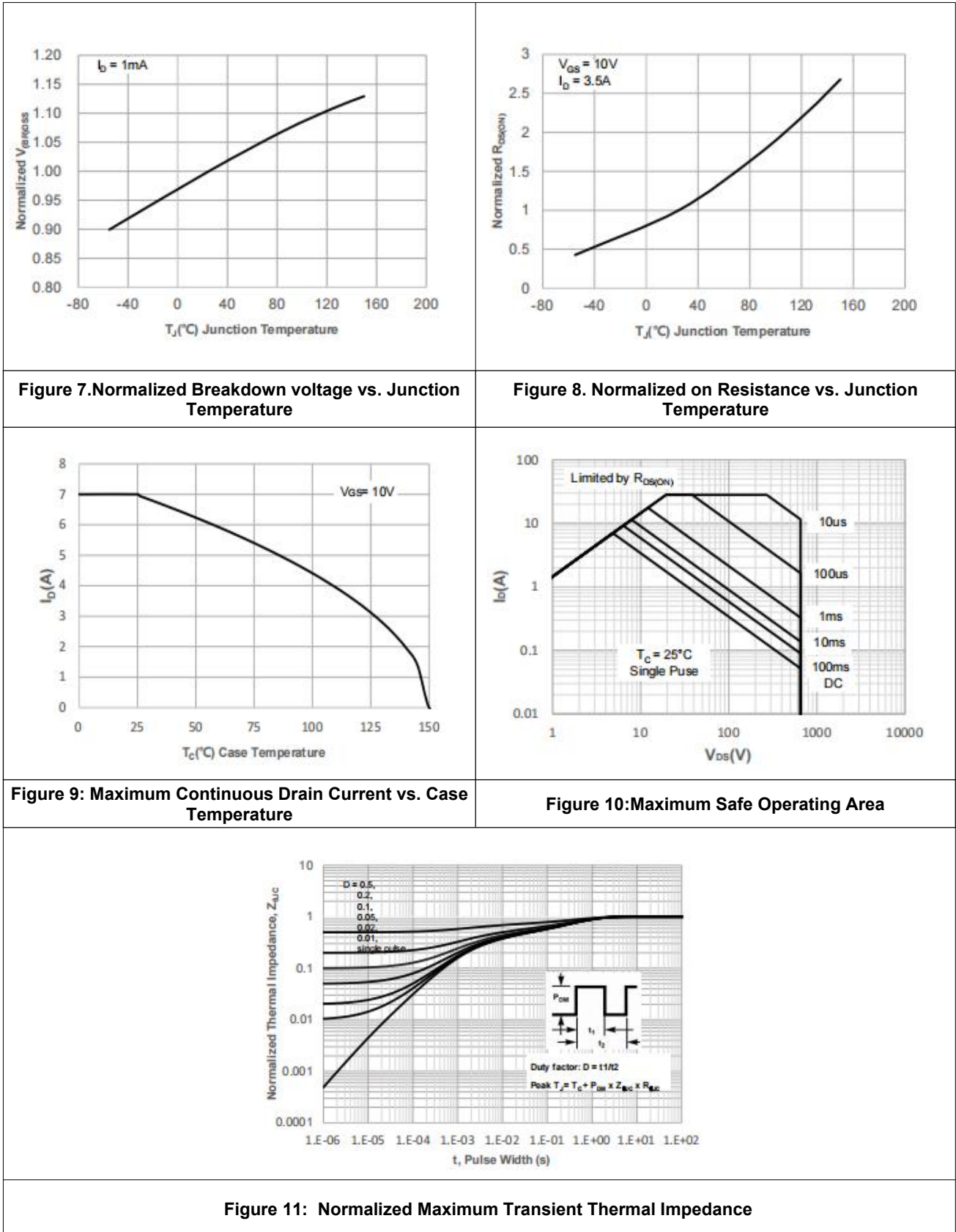
Figure 6. Capacitance Characteristics



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■ Characteristic Curve



Package Information

TO-252

